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Kind regards,

Team Nexperia

PSMN6R5-80PS

N-channel 80 V 6.9 m Ω standard level MOSFET in TO220

Rev. 02 — 1 November 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in TO220 package qualified to 175 °C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for standard level gate drive sources

1.3 Applications

- DC-to-DC converters
- Motor control
- Load switching
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	80	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; see Figure 1	[1]	-	100	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	-	210	W
T _j	junction temperature		-55	-	175	°C
Static characteristics						
R _{DS(on)}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 15 A; T _j = 25 °C; see Figure 13	[2]	5.9	6.9	m Ω
Dynamic characteristics						
Q _{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 25 A;	-	16	-	nC
Q _{G(tot)}	total gate charge	V _{DS} = 40 V; see Figure 14 ; see Figure 15	-	71	-	nC
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 49 A; V _{sup} ≤ 80 V; R _{GS} = 50 Ω ; unclamped	-	-	700	mJ

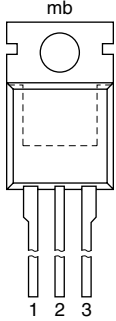
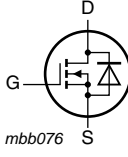
[1] Continuous current rating is limited by package.

[2] Measured 3 mm from package.



2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN6R5-80PS	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

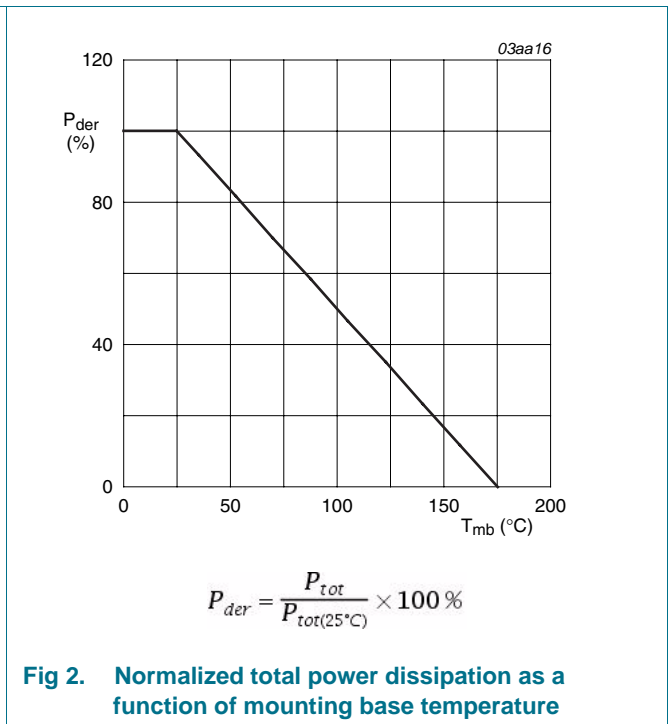
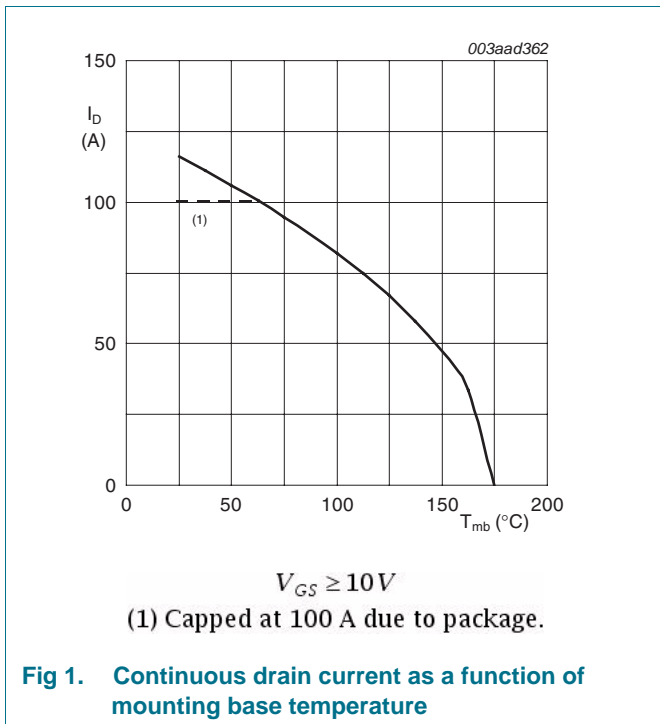
4. Limiting values

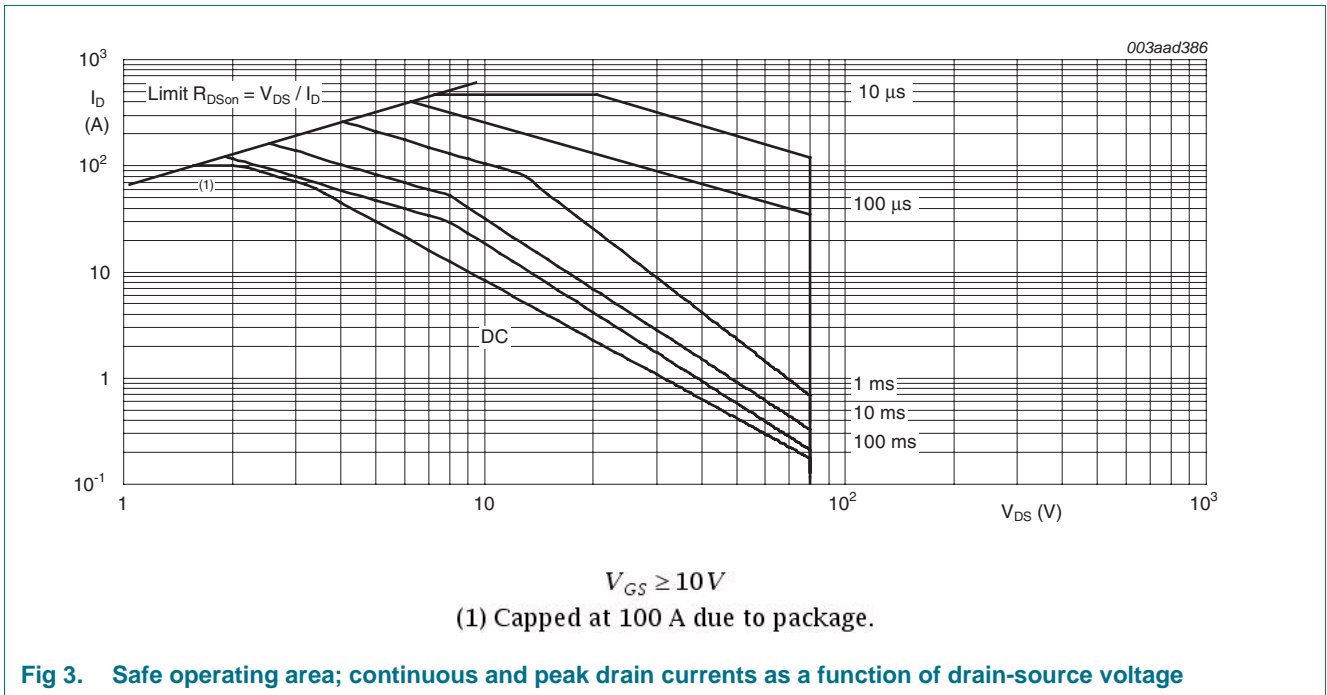
Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	80	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	80	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 100 °C; see Figure 1	-	82	A
		V _{GS} = 10 V; T _{mb} = 25 °C; see Figure 1 [1]	-	100	A
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see Figure 3	-	470	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	210	W
T _{stg}	storage temperature		-55	175	°C
T _j	junction temperature		-55	175	°C
Source-drain diode					
I _S	source current	T _{mb} = 25 °C	-	100	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C	-	470	A
Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(initial)} = 25 °C; I _D = 49 A; V _{sup} ≤ 80 V; R _{GS} = 50 Ω; unclamped	-	700	mJ

[1] Continuous current rating is limited by package.

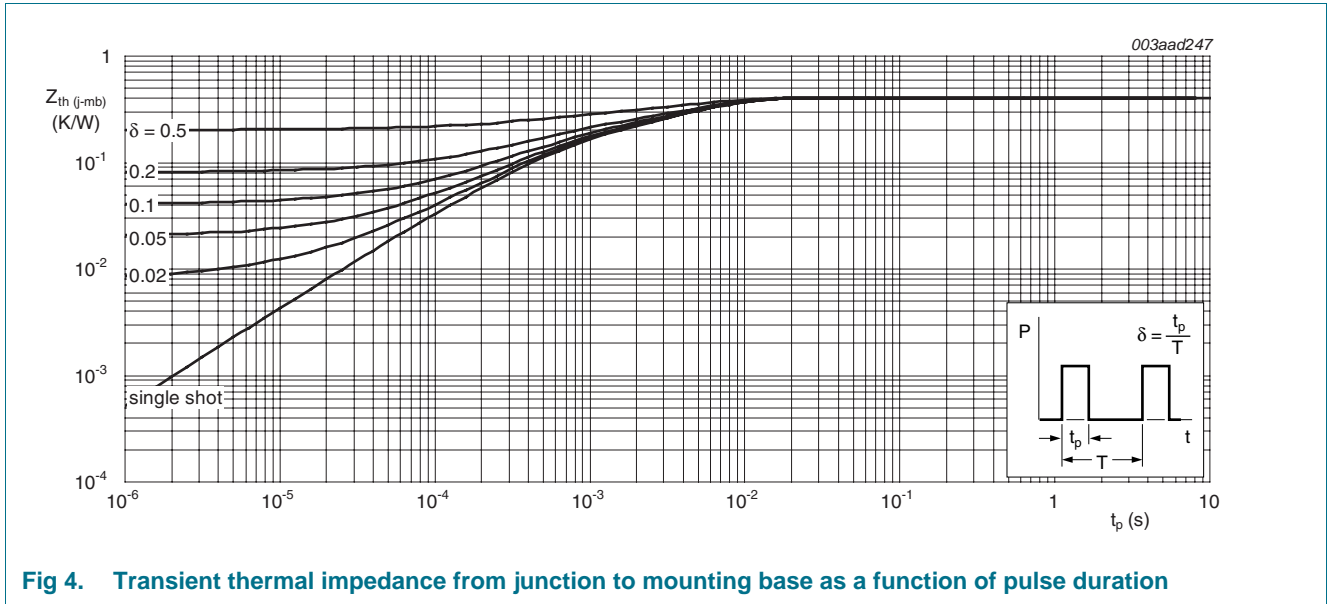




5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	0.4	0.7	K/W



6. Characteristics

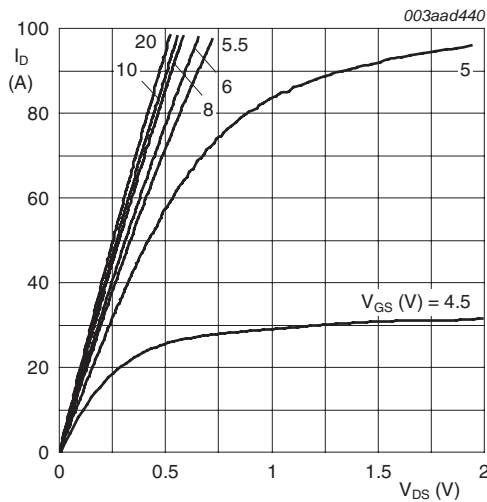
Table 6. Characteristics
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	73	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	80	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11	-	-	4.6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11	2.3	3	4	V
I_{DSS}	drain leakage current	$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.3	10	μA
		$V_{DS} = 80 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$	-	-	150	μA
I_{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ see Figure 12	-	-	11.5	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 12	-	-	16.56	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 13	[1]	-	5.9	6.9
R_G	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	0.75	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	61	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 ; see Figure 15	-	71	-	nC
Q_{GS}	gate-source charge		-	19	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	13.2	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	5.8	-	nC
Q_{GD}	gate-drain charge		-	16	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 25 \text{ A}; V_{DS} = 40 \text{ V};$ see Figure 15	-	4.3	-	V
C_{iss}	input capacitance	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 16	-	4461	-	pF
C_{oss}	output capacitance		-	410	-	pF
C_{rss}	reverse transfer capacitance		-	214	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 40 \text{ V}; R_L = 0.5 \text{ } \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 4.7 \text{ } \Omega$	-	26	-	ns
t_r	rise time		-	24	-	ns
$t_{d(off)}$	turn-off delay time		-	57	-	ns
t_f	fall time		-	22	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 17	-	0.79	1.2	V

Table 6. Characteristics ...continued
 Tested to JEDEC standards where applicable.

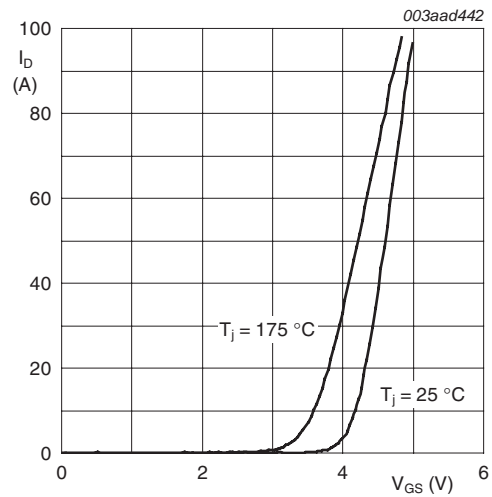
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
t_{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = 100 \text{ A}/\mu\text{s}$;	-	48	-	ns
Q_r	recovered charge	$V_{GS} = 0 \text{ V}$; $V_{DS} = 40 \text{ V}$	-	82	-	nC

[1] Measured 3 mm from package.



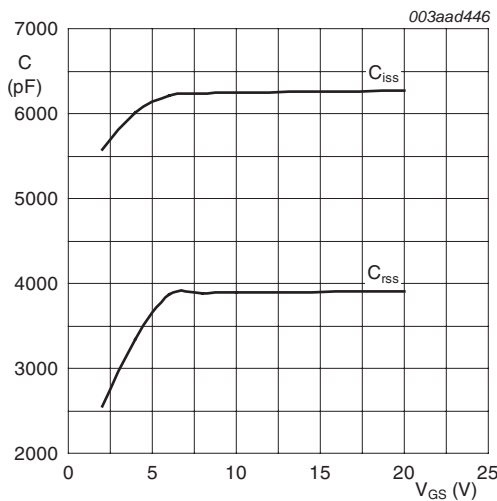
$T_j = 25^\circ\text{C}$; $t_p = 300\mu\text{s}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



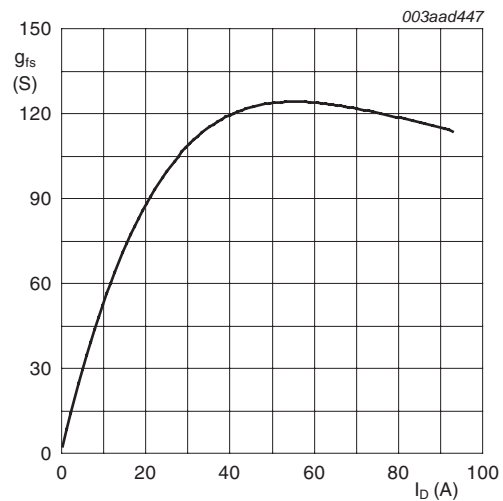
$V_{DS} = 15\text{V}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



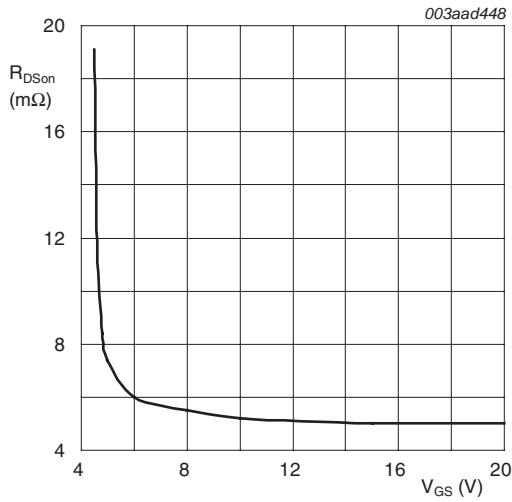
$V_{DS} = 0\text{V}$; $f = 1\text{MHz}$

Fig 7. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



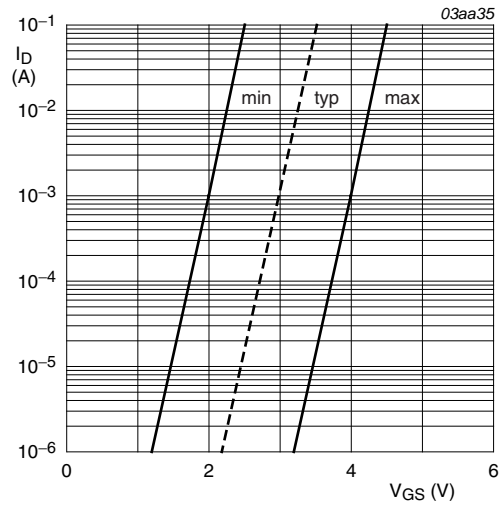
$T_j = 25^\circ\text{C}$; $V_{DS} = 15\text{V}$

Fig 8. Forward transconductance as a function of drain current; typical values



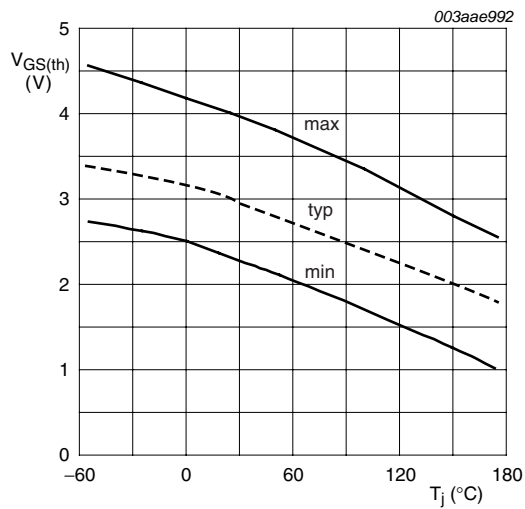
$T_j = 25\text{ }^\circ\text{C}; I_D = 25\text{ A}$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



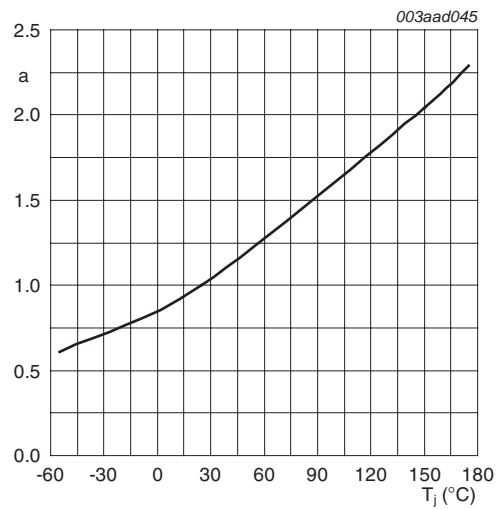
$T_j = 25\text{ }^\circ\text{C}; V_{DS} = 5\text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



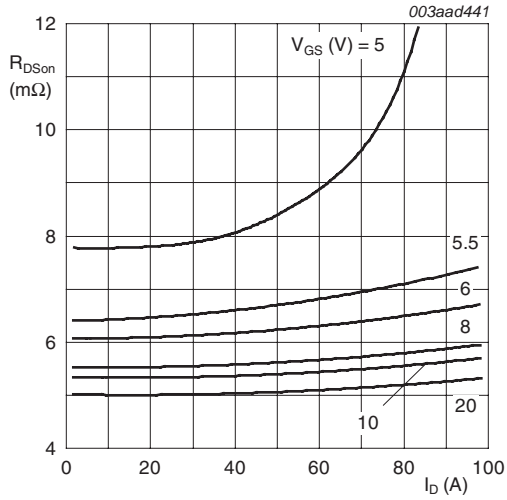
$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature



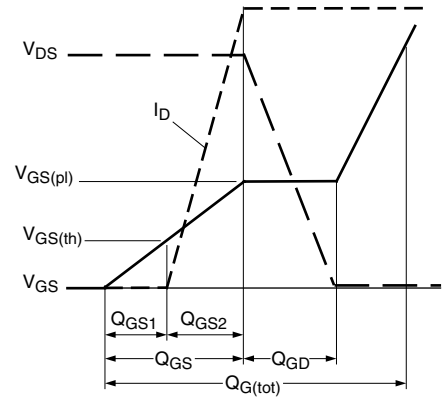
$$a = \frac{R_{DS(on)}}{R_{DS(on)@25^\circ\text{C}}}$$

Fig 12. Normalized drain-source on-state resistance factor as a function of junction temperature



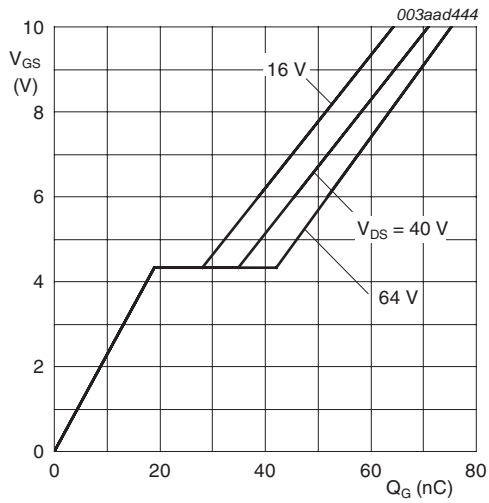
$T_j = 25^\circ C; t_p = 300 \mu s$

Fig 13. Drain-source on-state resistance as a function of drain current; typical values



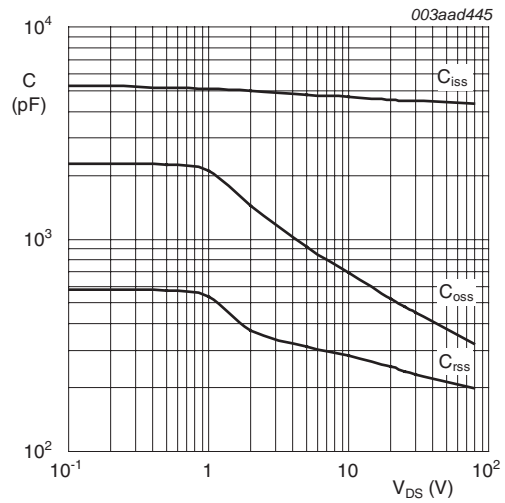
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Fig 14. Gate charge waveform definitions



$T_j = 25^\circ C; I_D = 25 A$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0 V; f = 1 MHz$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

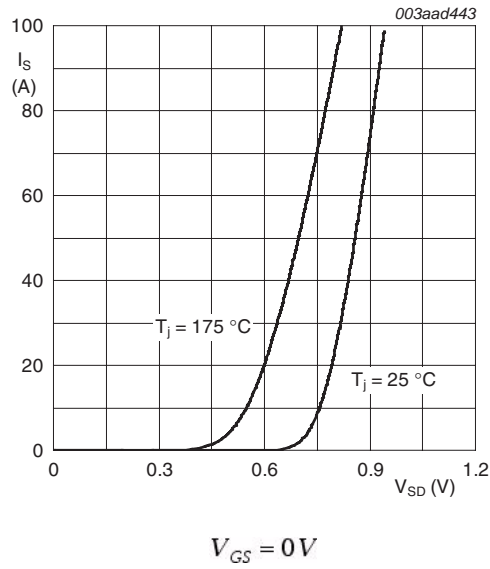


Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

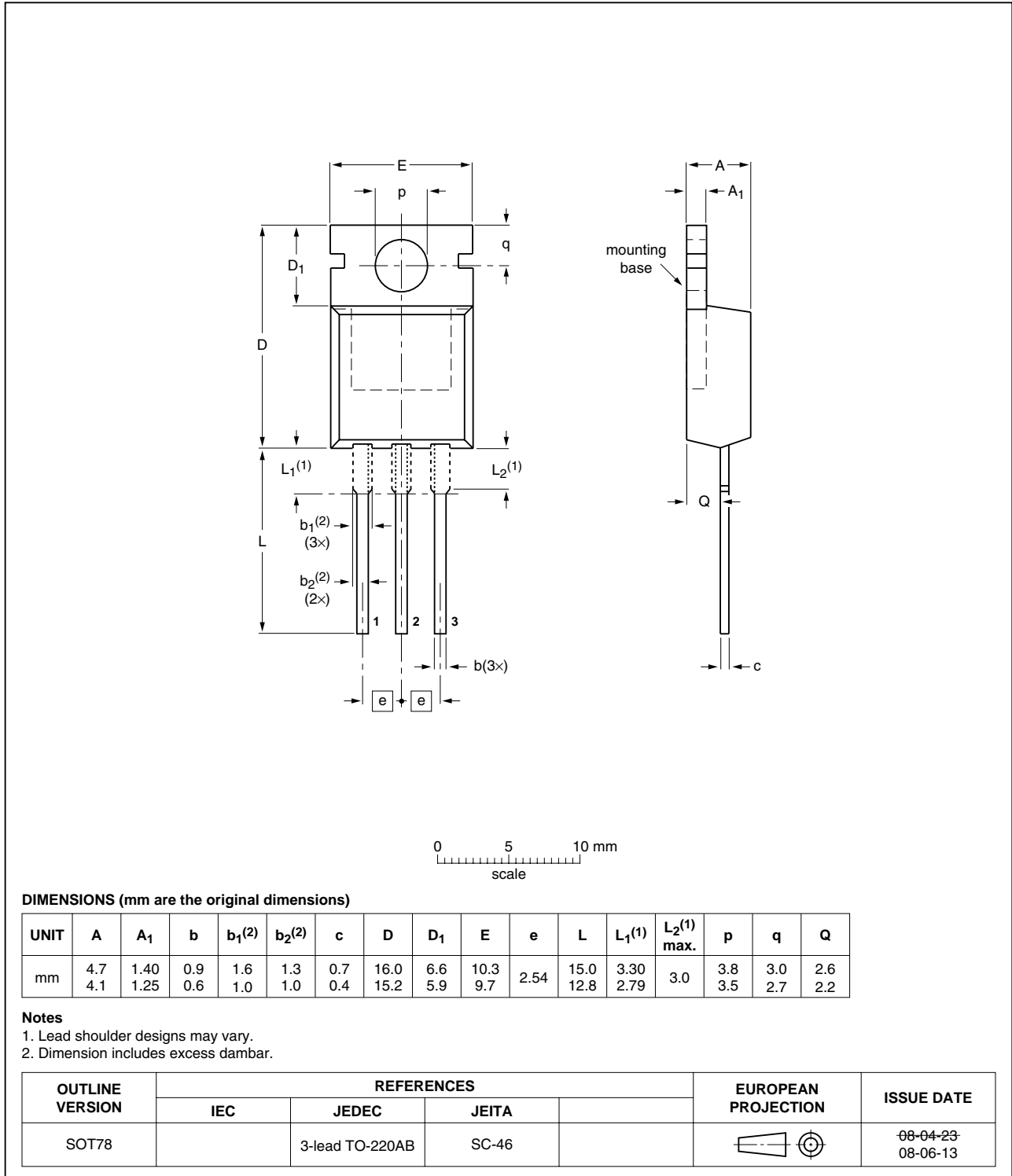


Fig 18. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN6R5-80PS v.2	20101101	Product data sheet	-	PSMN6R5-80PS v.1
Modifications:	<ul style="list-style-type: none">• Status changed from objective to product.• Various changes to content.			
PSMN6R5-80PS v.1	20100309	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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